

# Progress in Thick GEM-like (THGEM)-based Detectors

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## MOTIVATION:

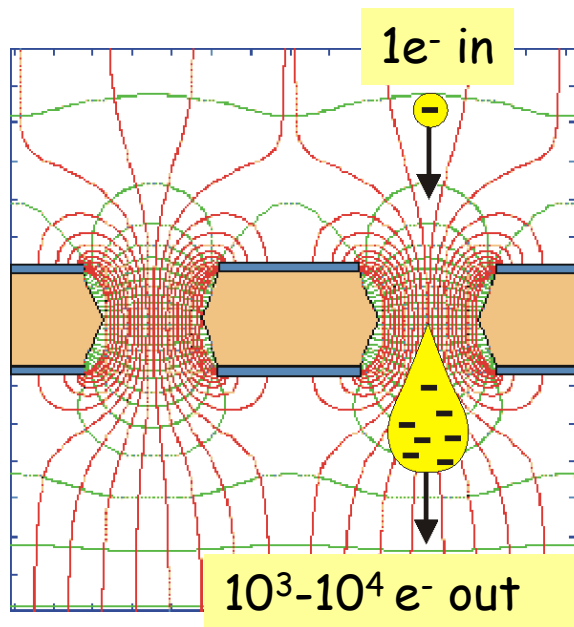
Robust, economic, large-area radiation imaging detectors

FAST, HIGH-RATE, MODERATE LOCALIZATION RESOLUTION



# Gaseous multiplication in holes

- Avalanche confined within a small volume
- Secondary effects confined/reduced -> high gains
- True pixilated structures
- Possibility to CASCADE multipliers -> further higher gains



High electric field in the holes

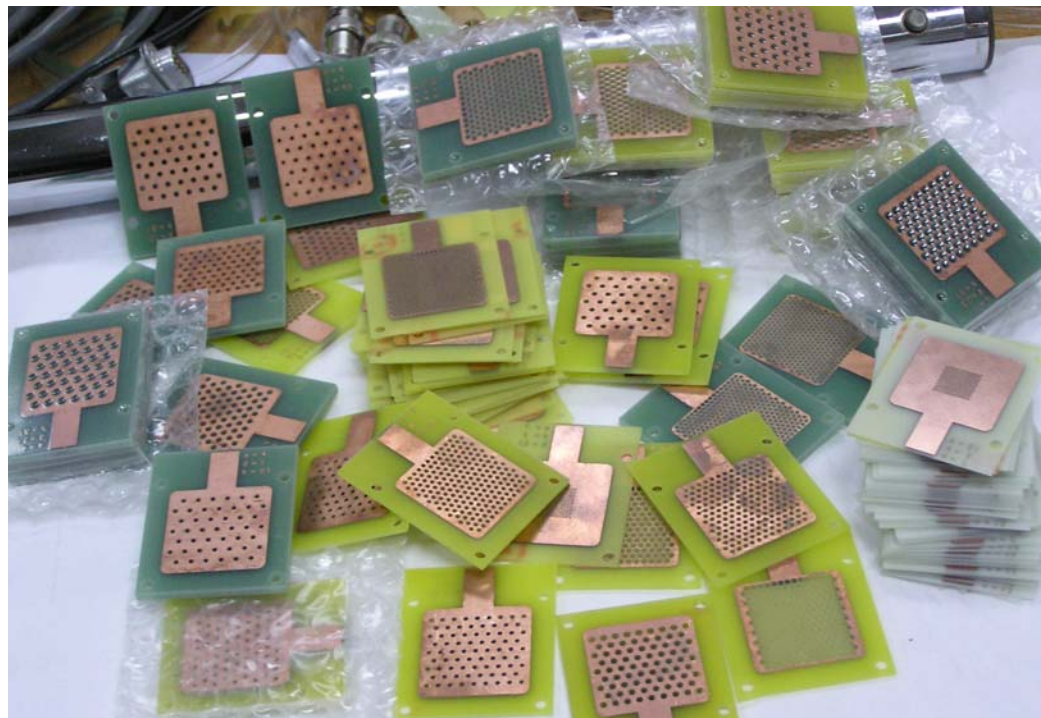
- Breskin, Charpak NIM108(1973)427 Discharge in glass capillaries
- Lum et al. IEEE NS27(1980)157, & Del Guerra et al. NIMA257(1987)609 Avalanches in holes
- Sakurai et al. NIMA374(1996)341, Glass Capillary plates & Peskov et al. NIMA433(1999)492
- ☀ Sauli NIMA386(1997)531
- Ostling, Peskov et al, IEEE NS50(2003)809 G-10 "Capillary plates"
- ☀ Chechik et al. NIMA535(2004)303 & Physics/0502131



# Thick GEM-like multipliers: THGEM

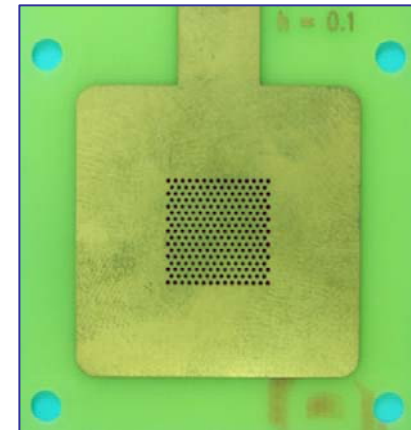
R. Chechik et al. NIM A535 (2004) 303-308  
& R. Chechik et al. NIM A553 (2005) 35-40

Manufactured by standard PCB techniques of **precise drilling** in G-10 (+other materials) and **Cu etching**.



**ECONOMIC & ROBUST !**

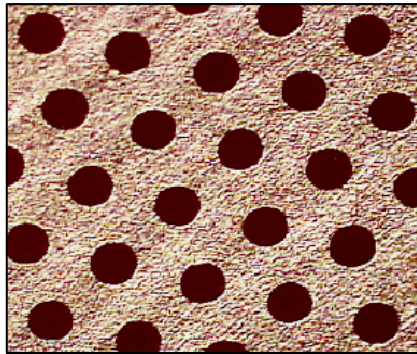
Hole diameter  $d = 0.3 - 1 \text{ mm}$   
Dist. Bet. holes  $a = 0.7 - 4 \text{ mm}$   
Plate thickness  $t = 0.4 - 3 \text{ mm}$



A small THGEM costs ~3\$ /unit.  
With minimum order of 400\$ → ~120 THGEMs.  
~10 times cheaper than standard GEM.

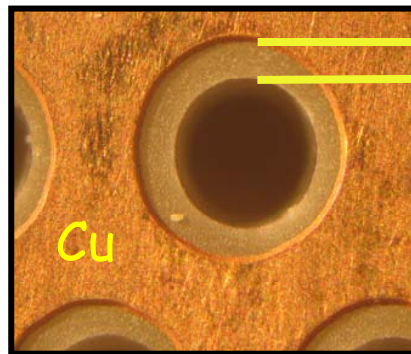


Standard GEM  
 $10^3$  gain in  
single GEM



1mm

THGEM  
 $10^5$  gain in  
single-THGEM



Important:  
0.1mm G-10 rim.  
reduces discharges  
-> high gains!

## Is THGEM an "Expanded" GEM ?

### expanded

- The dimensions

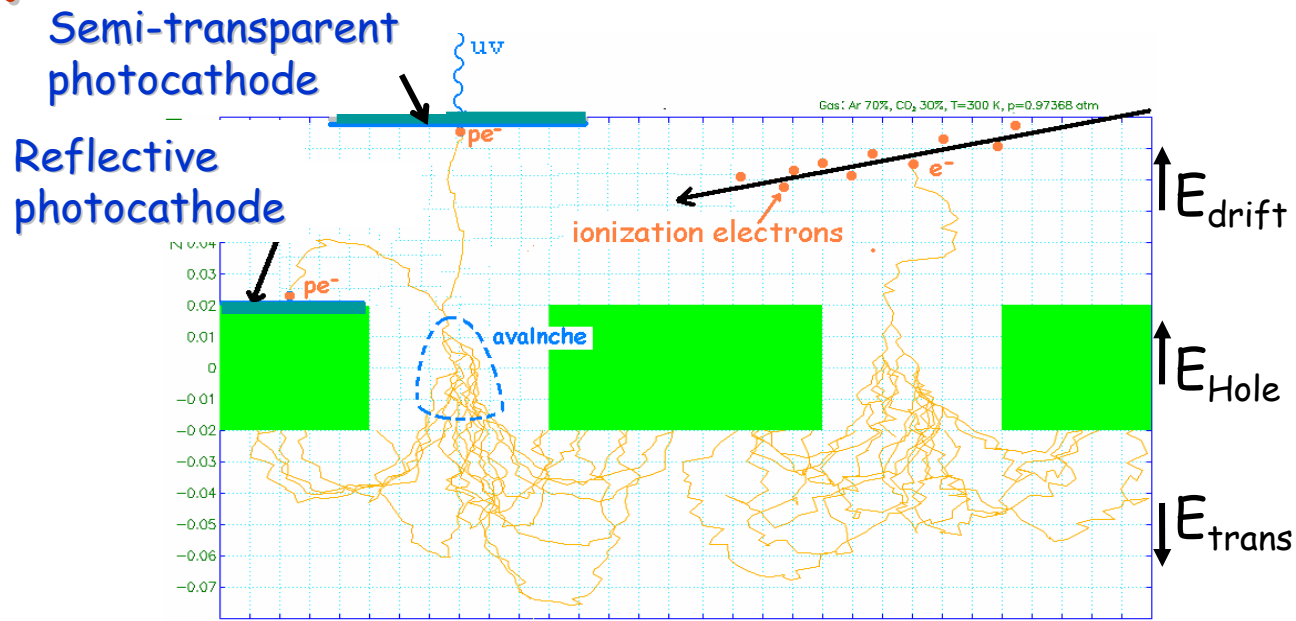
### does not scale up

- Electron diffusion & transport
- Electric fields
- Gain
- Timing properties
- Rate capability
- Ions transport

**It is a new device that has to be studied.**



# Operation mechanism (role of all fields)



Garfield simulation of electron multiplication in Ar/CO<sub>2</sub> (70:30)

Need to study the effect of all fields on:  
 $e^-$  and ion transport in/out holes

- > efficiency to single-electron events
- > cascade THGEMs
- > ion backflow to the conversion gap

Electric fields at photocathode surface

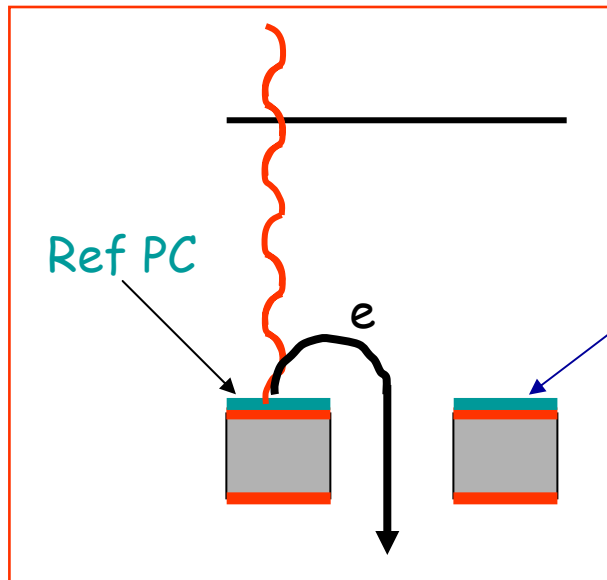
- > operation with solid photocathode

Gain, signal rise-time, rate capability, localization, etc





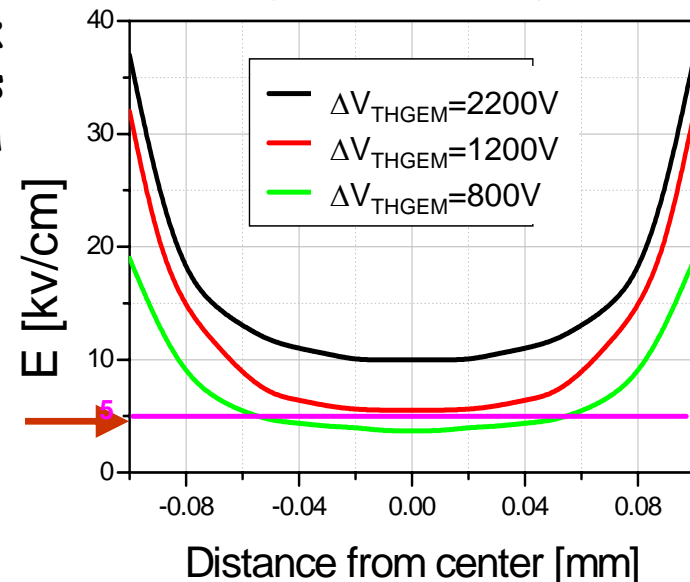
# Example: Photon detector w reflective CsI PC deposited on the THGEM top face (e.g. RICH photon detectors)



0.4mm thick  
0.3mm holes  
0.7mm pitch

Electric field on photocathode surface created by the hole dipole field

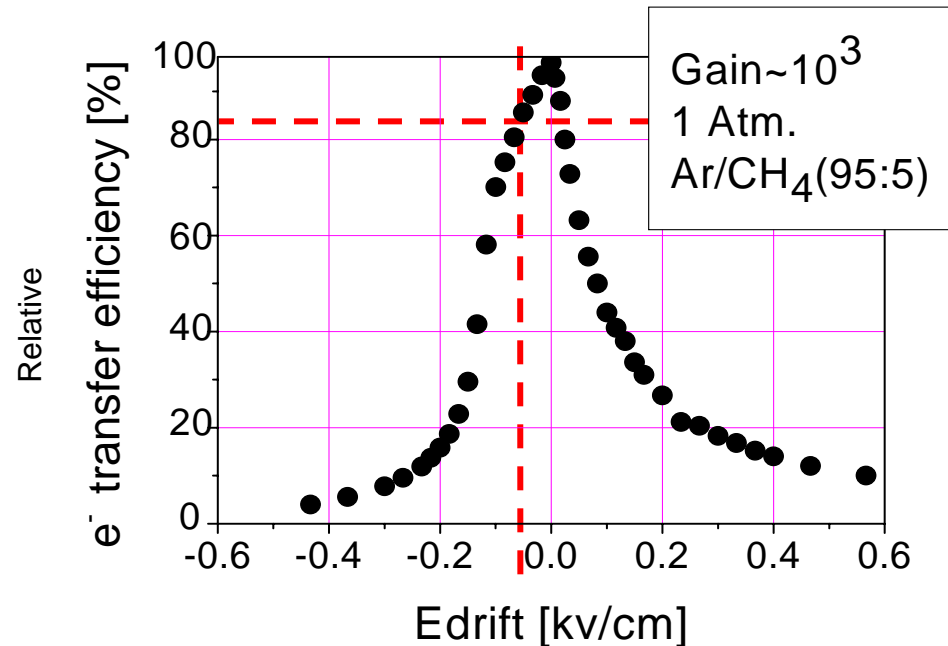
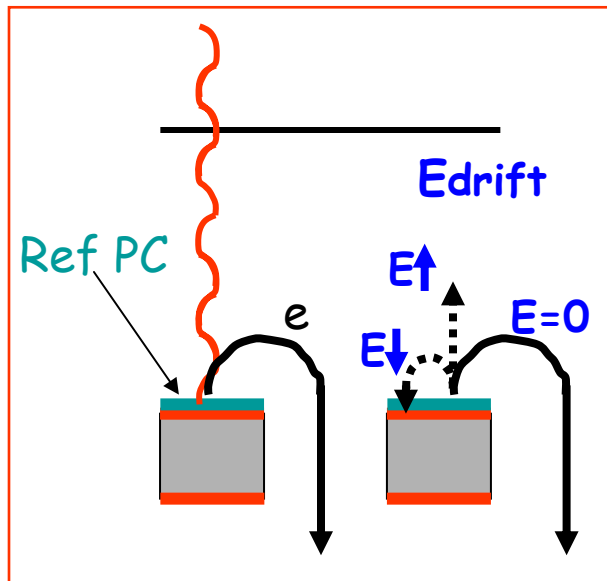
>3kV/cm



- Require:
- High field on the PC surface (for high QE).
  - Good  $e^-$  focusing into the holes (for high detection efficiency).
  - Low sensitivity for ionizing background radiation (e.g. RICH).



# Photon detector w reflective CsI PC deposited on the THGEM top face (2)

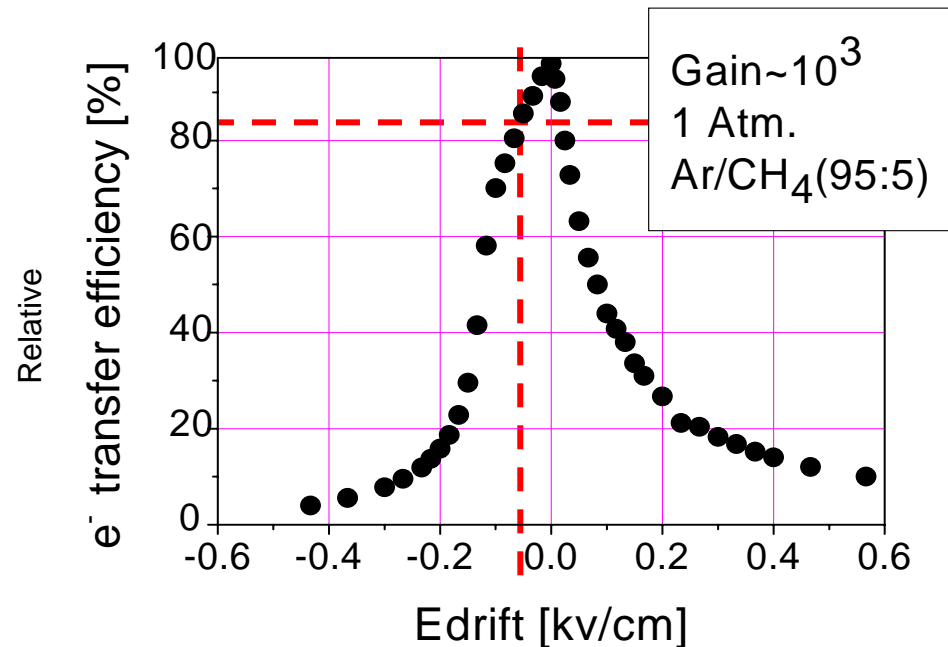
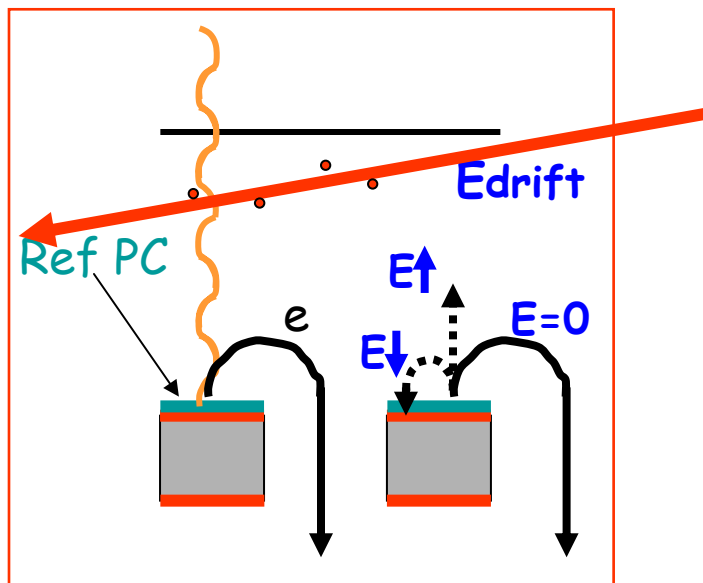


**Focusing is done by hole dipole field.**

- Maximum efficiency at  $E_{drift} = 0$ .
- Slightly reversed  $E_{drift}$  (50-100V/cm)  
good photoelectron collection low sensitivity to MIPS !



# Photon detector w reflective CsI PC deposited on the THGEM top face (2)



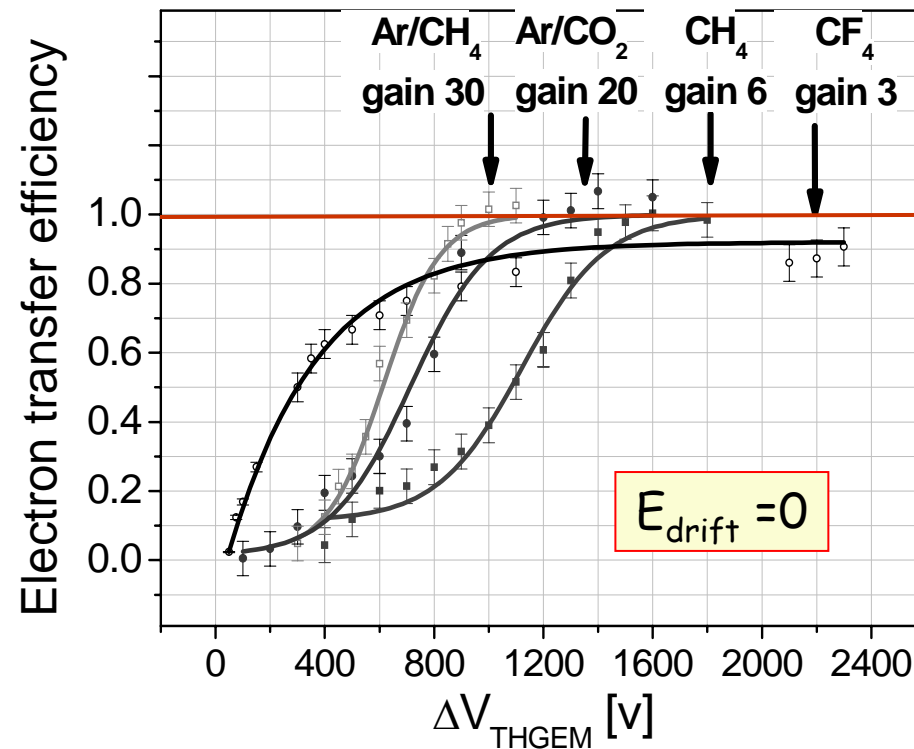
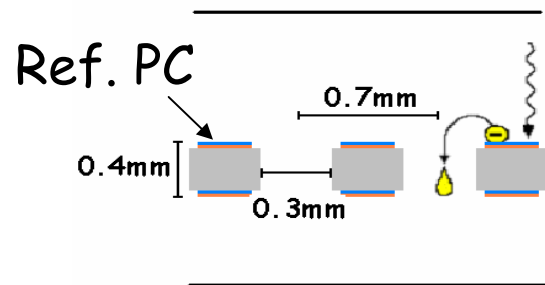
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# Single-THGEM: $e^-$ transport into holes. Role of $E_{\text{hole}}$



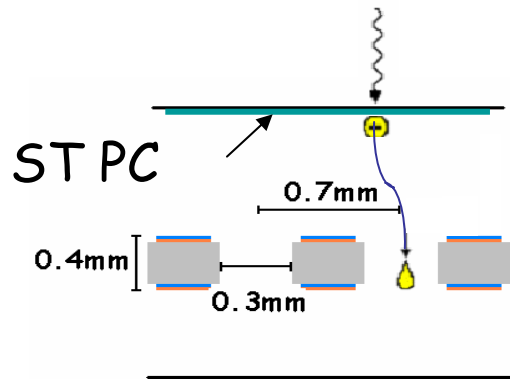
Full electron transfer efficiency into the holes, already at low gain.

-> good single-electron detection efficiency

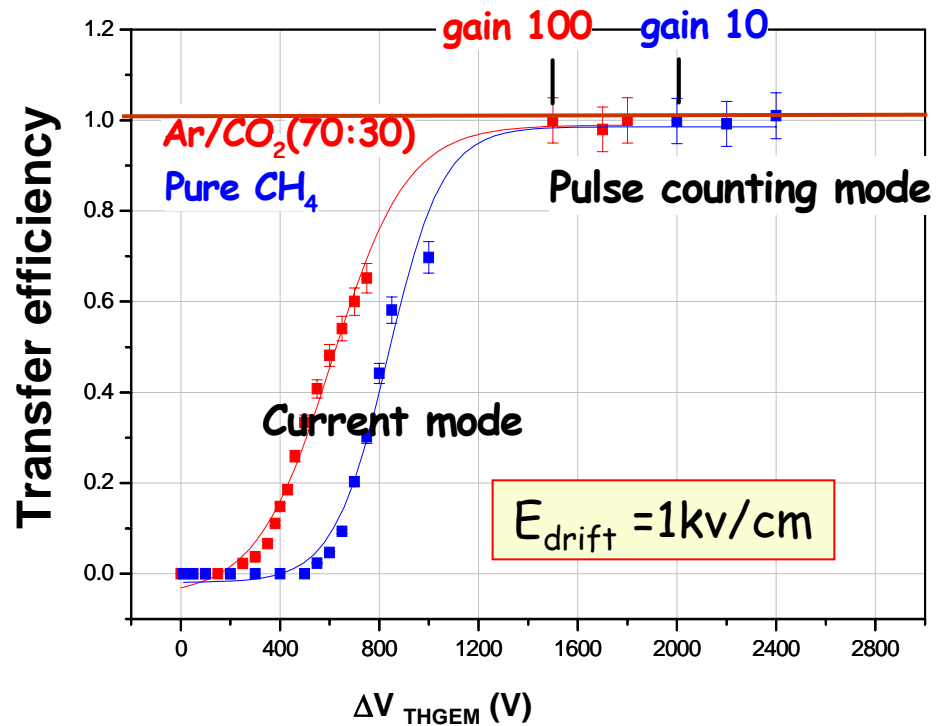
-> good energy resolution with highly ionizing radiation



# Single-THGEM: e- transport into holes. Role of $E_{\text{hole}}$ (2)



With STPC require:  
 $E_{\text{drift}} \sim 1\text{kv/cm}$



Full electron transfer efficiency into the holes, already at low gain.

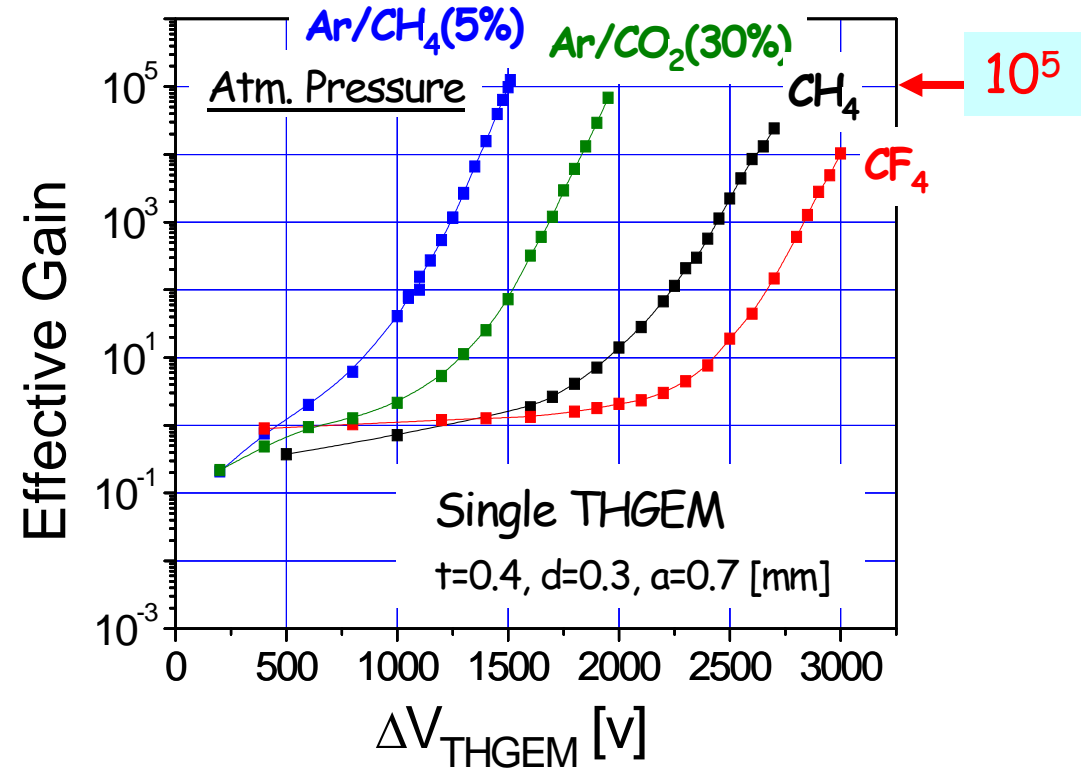
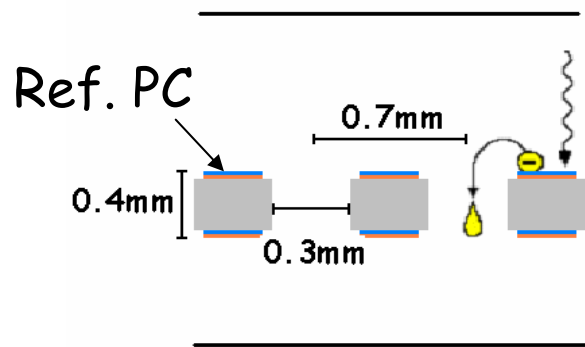
- > good single-electron detection efficiency
- > good energy resolution with highly ionizing radiation



# Single-THGEM: gain

Example: THGEM photon detector with reflective CsI photocathode.

R. Chechik et al. NIMA553 (2005) 35-40

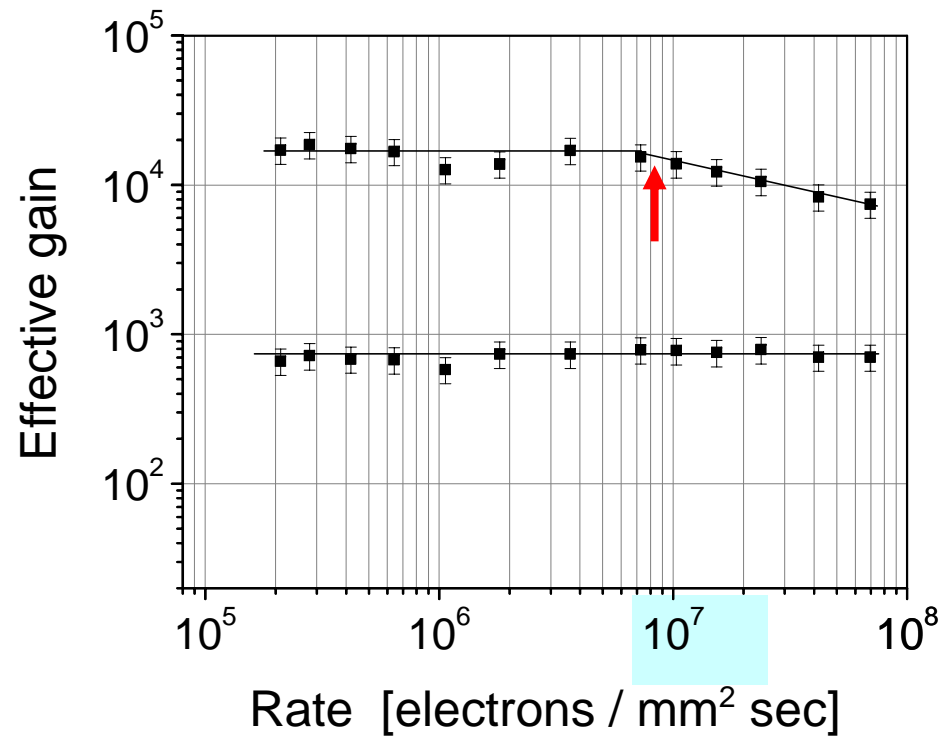
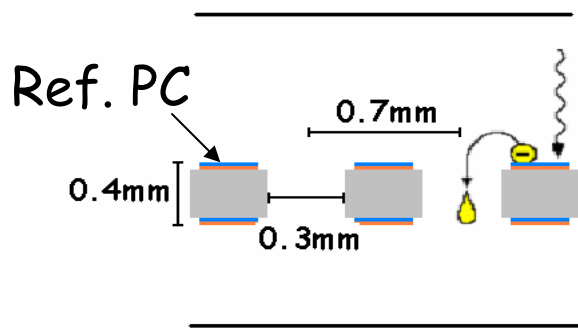


- Gain up to  $10^4$ - $10^5$  with single electrons (sparks)

Similar gain w ST PC.



# Single-THGEM: counting rate

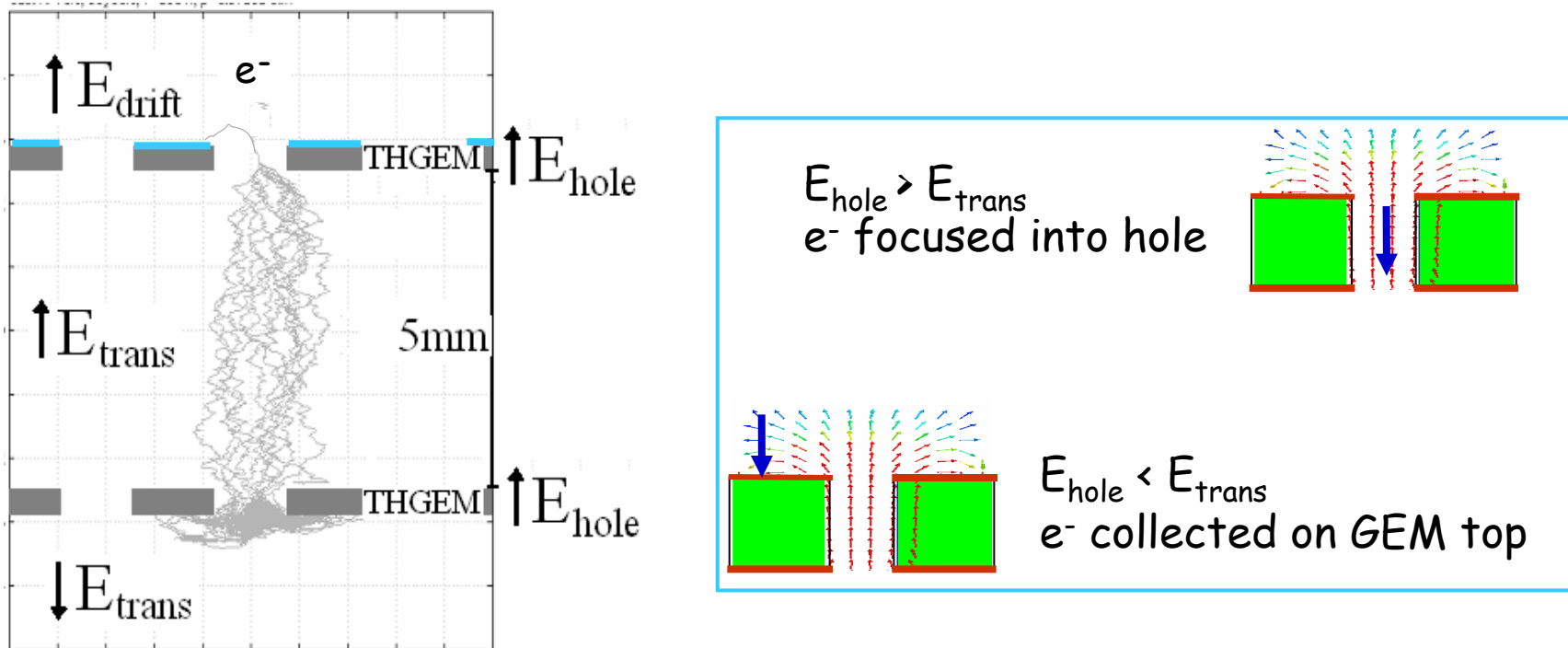


- Signal rise time < 10ns
- Rate capability: ~10MHz/mm<sup>2</sup> (space charge)



# Double-THGEM: Cascaded operation role of $E_{trans}$

C. Shalem et al. NIM A558 (2006) 475-489



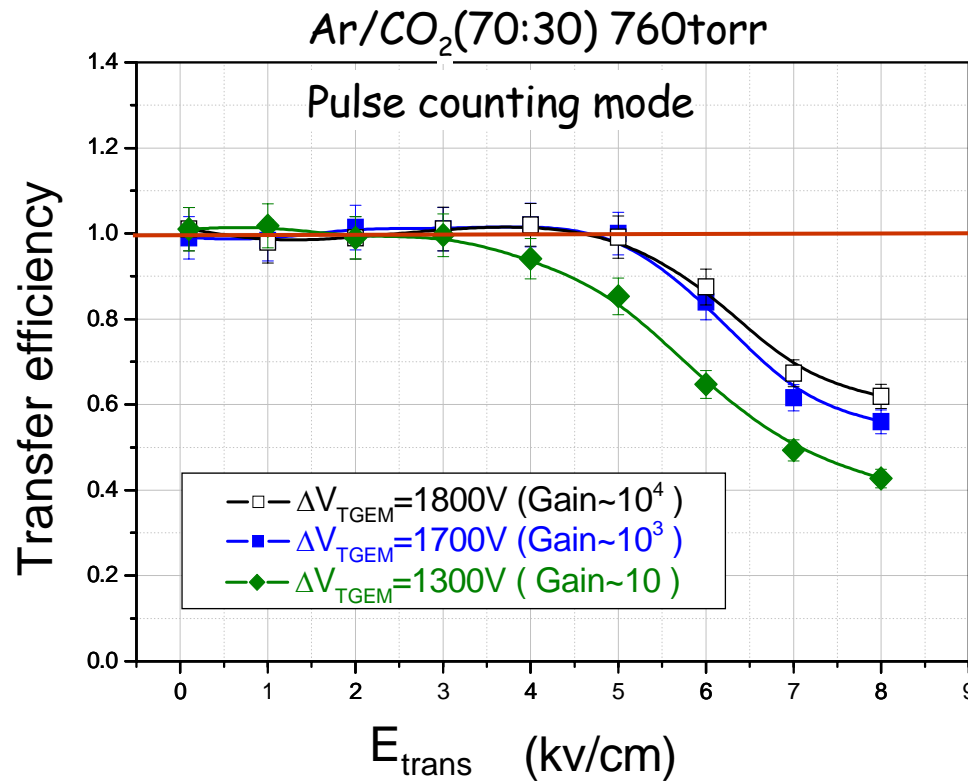
Require: Large  $E_{trans}$  for good extraction from THGEM<sub>1</sub>  
Small  $E_{trans}$  for good focus sing into THGEM<sub>2</sub>  
→ Optimization



# Double-THGEM: cascaded operation

## Role of $E_{\text{trans}}$ (2)

Both  
0.4mm thick  
0.3mm holes  
0.7mm pitch



efficient transfer to the 2<sup>nd</sup> THGEM:

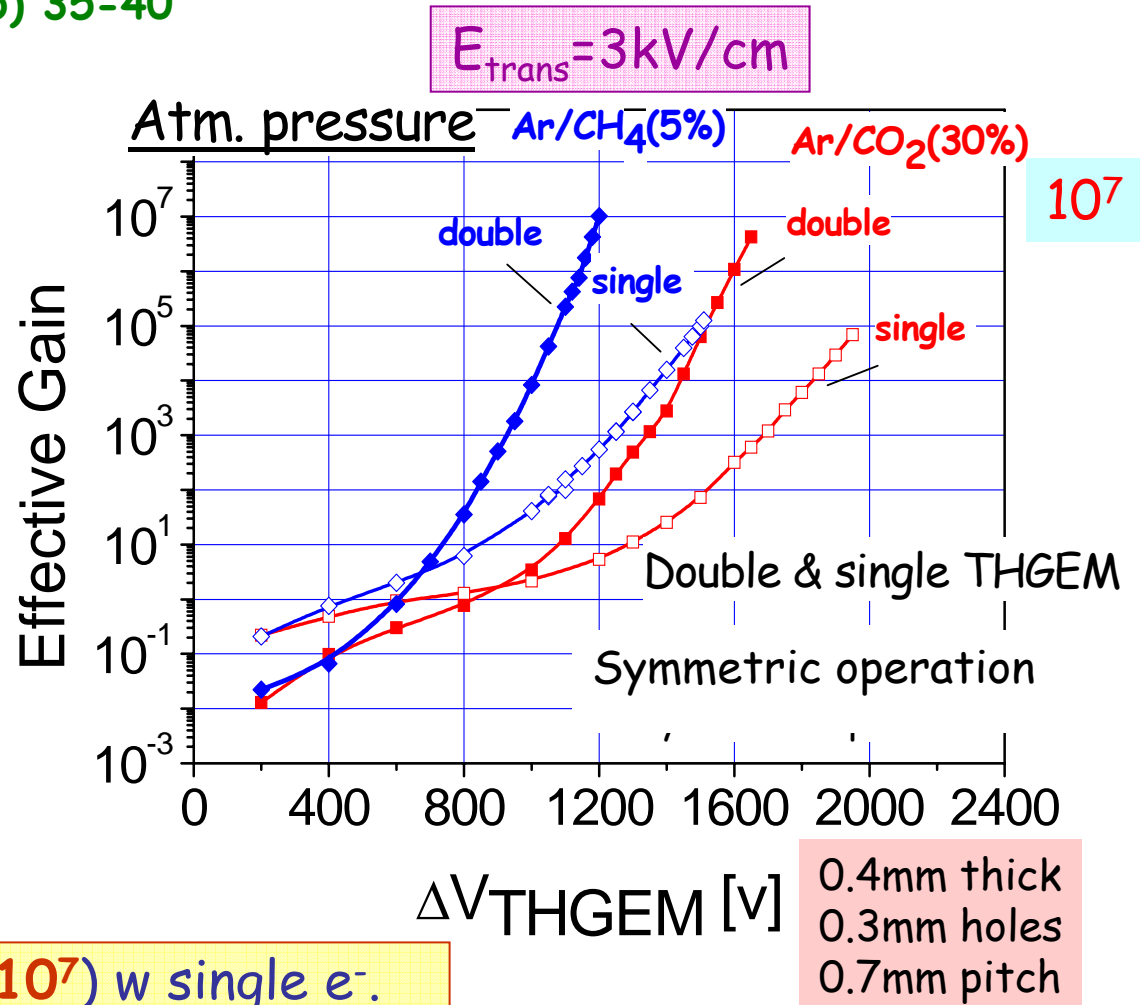
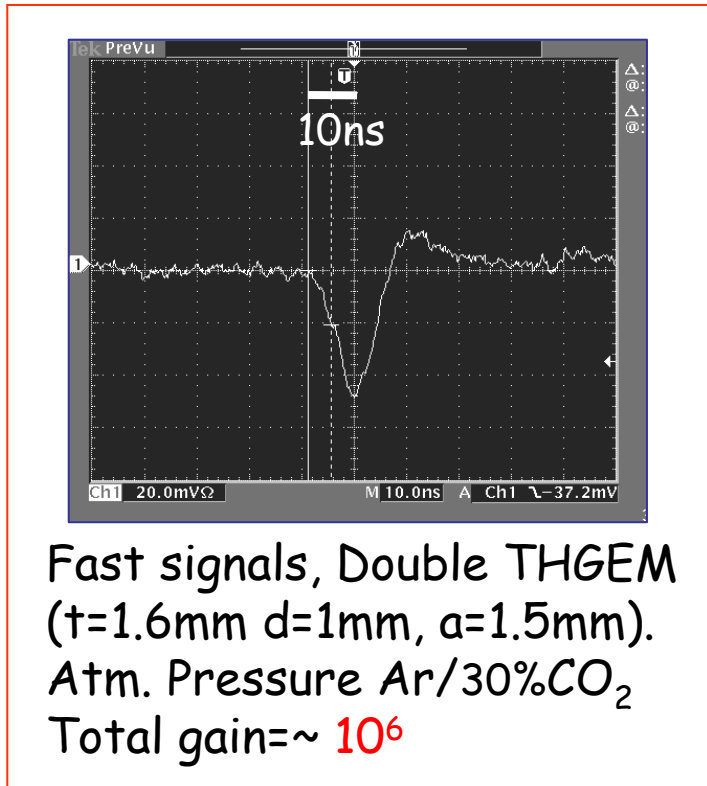
- up to high  $E_{\text{trans}}$  (e.g. 3kV/cm).
- at relatively low THGEM gains.





# Double-THGEM multiplier: Gain, rise time

R. Chechik et al. NIMA553 (2005) 35-40

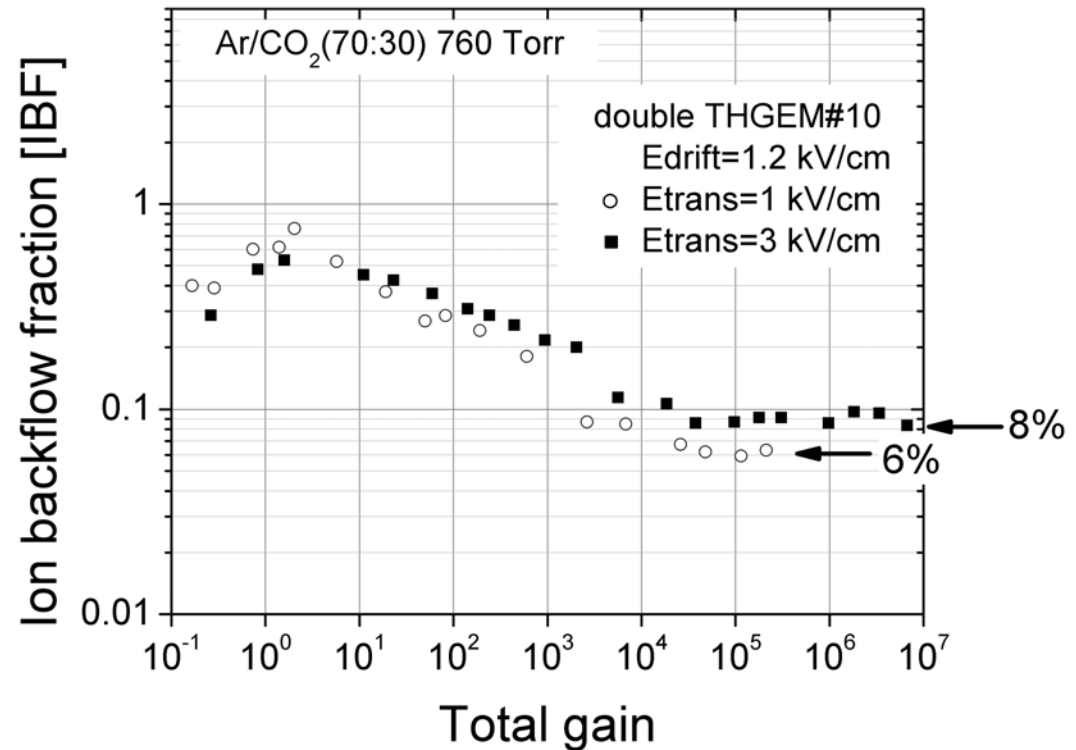
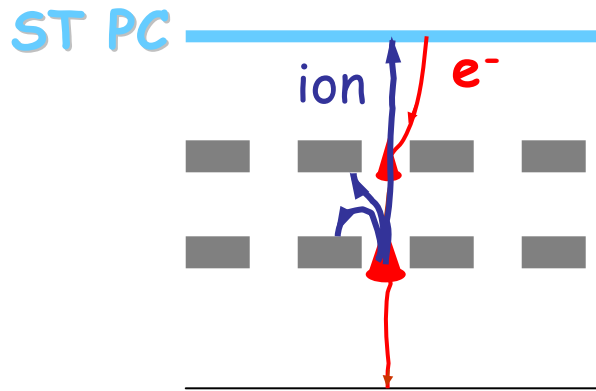


- Higher total gain ( $10^6 - 10^7$ ) w single  $e^-$ .
- $>10^3$  higher gain at same  $\Delta V_{\text{THGEM}}$
- Better stability



# Double-THGEM multiplier: ion backflow

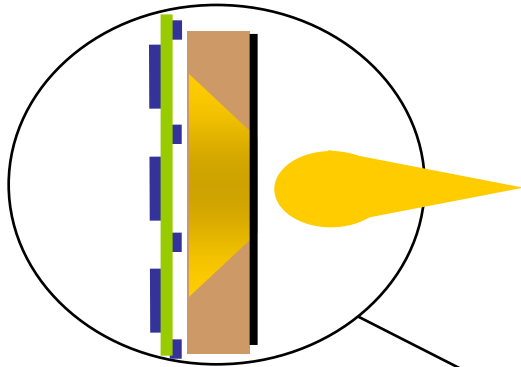
C. Shalem et al. NIM A558 (2006) 475-489



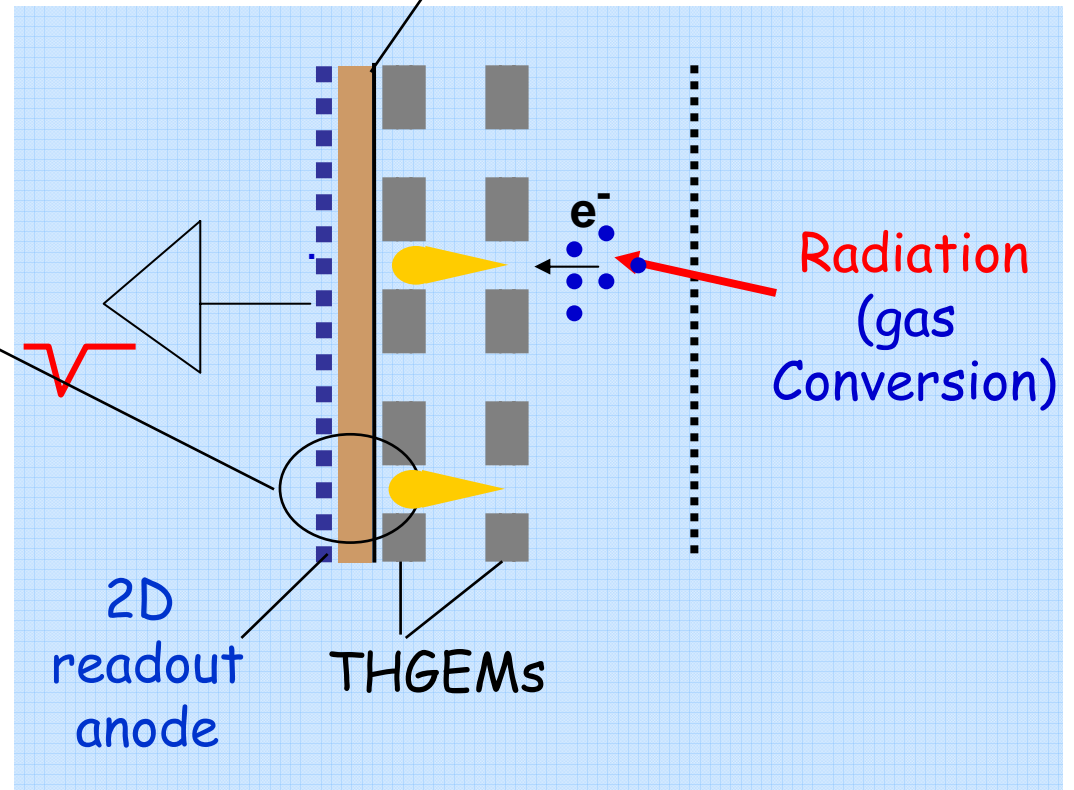
Ion backflow smaller than with 4-GEM multiplier.  
Prolonged PC life-time.



# 2D double-THGEM detector: a flat imaging detector



Resistive anode (e.g. C paint sprayed on PCB)



## Resistive anode:

- Signal broadening
- HV decoupling
- Electronics spark protection

C paint  $\rightarrow$  3 M $\Omega$ /square

$\rightarrow$  ~70% charge transmission

evaporated Ge  $\rightarrow$  30 M $\Omega$ /square

$\rightarrow$  ~95% charge transmission

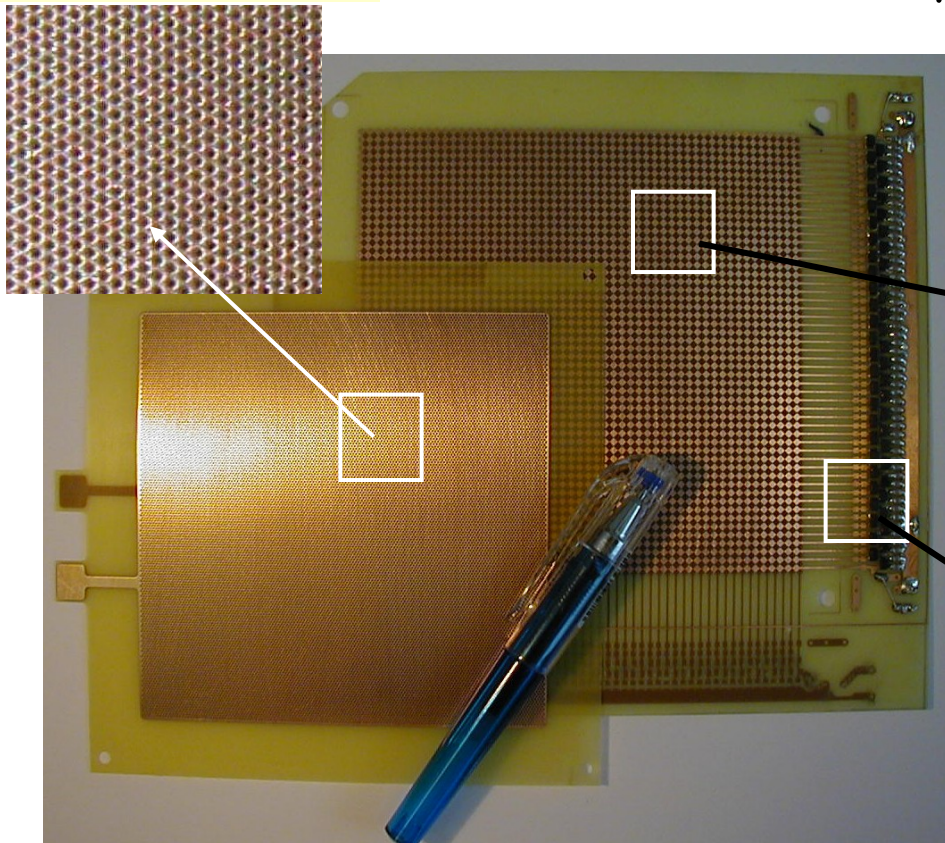
Simple and economic readout scheme.  
Induced-signal width matched to readout-pixel size.



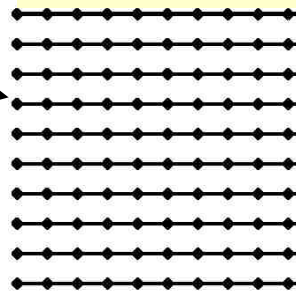
# 10x10 cm<sup>2</sup> 2D double-THGEM detector

- 2x 10x10cm<sup>2</sup> THGEM
- 2-sided pad-string anode (0.5mm thick)
- Delay-line readout (SMD)

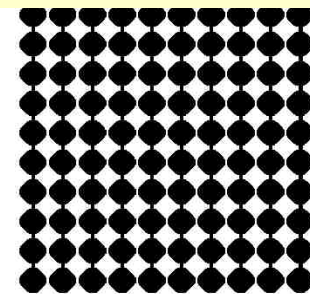
0.4mm thick,  
0.5mm  $\varnothing$  holes,  
1mm pitch



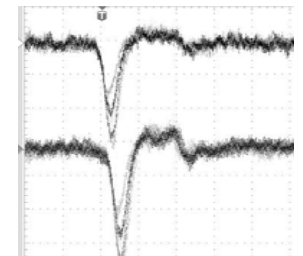
front side



back side



X & Y  
DL-signals



2 mm pitch, 1.35ns/mm



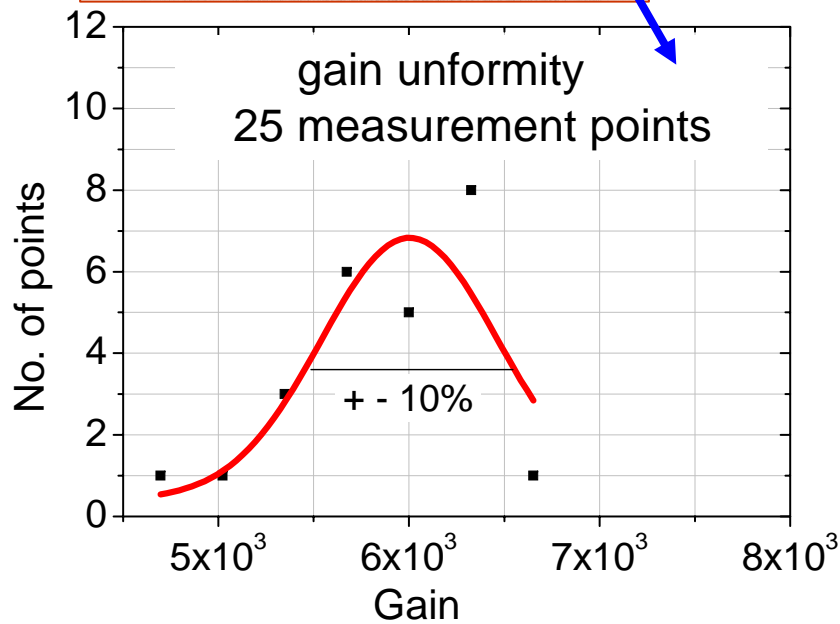
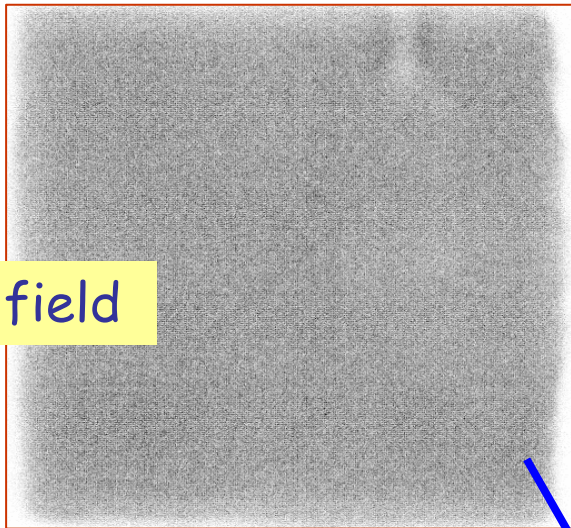


# Gain and uniformity

Ar/CH4 (95:5) 8keV x-rays  
Conversion gap = 10 mm, 1kV/cm  
Transfer Gap = 2 mm, 3.5 kV/cm  
Induction Gap = 1 mm, 4 kV/cm  
 $\Delta V_{\text{THGEM}} = 1210$  Volt

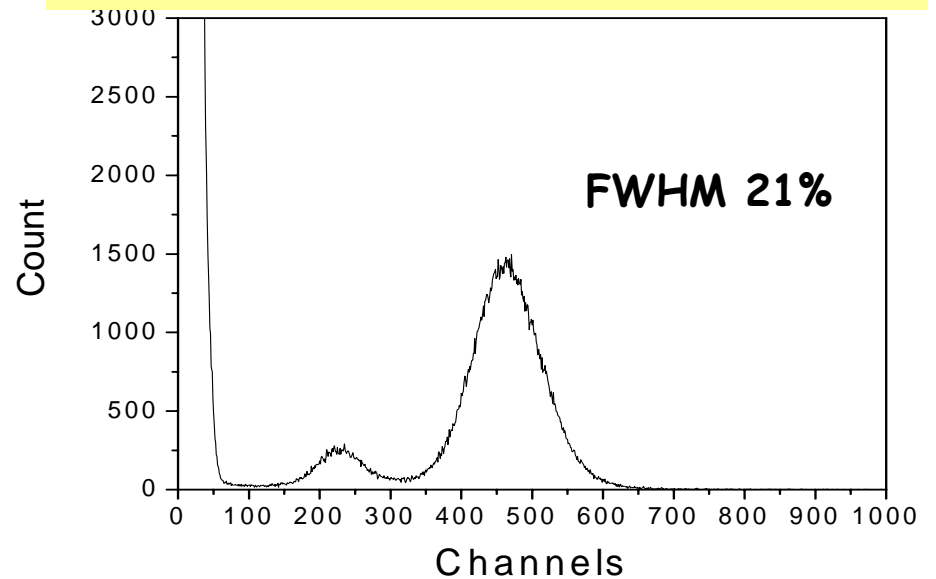
**Gain =  $6 \times 10^3$**

Flat field



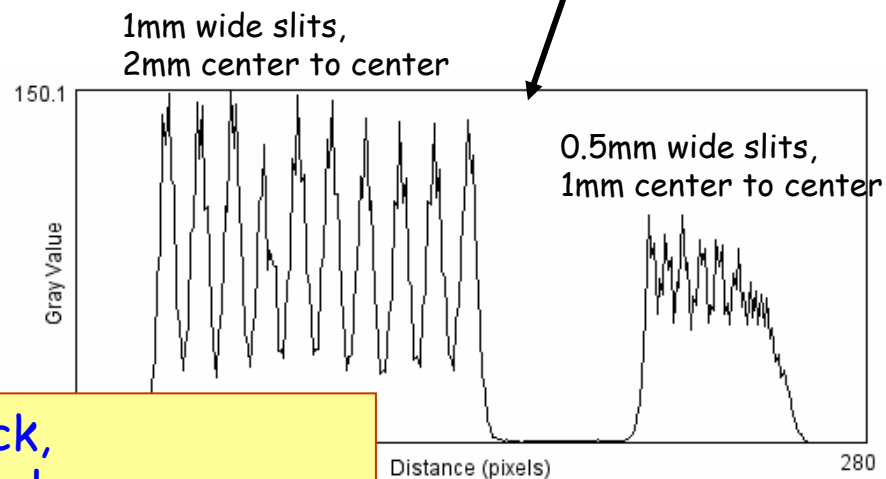
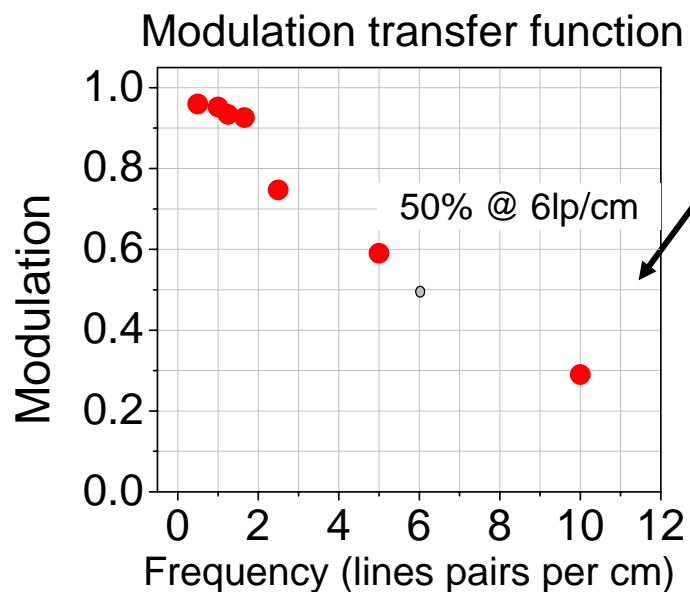
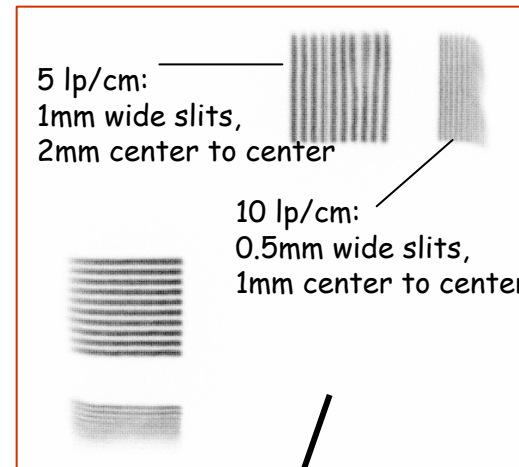
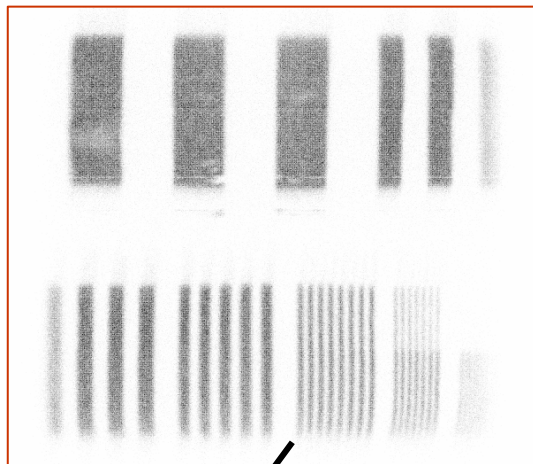
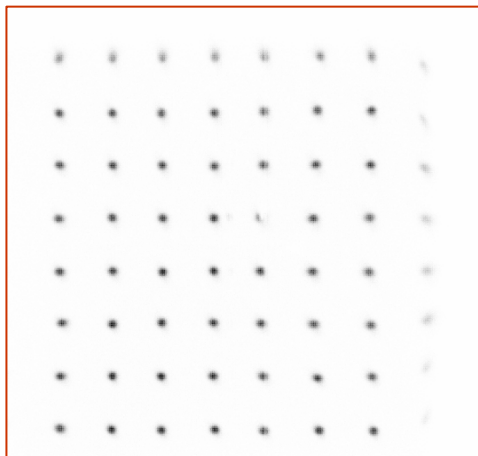
# Energy resolution

Local energy spectrum of 6 keV x-rays



# Localization : linearity, resolution

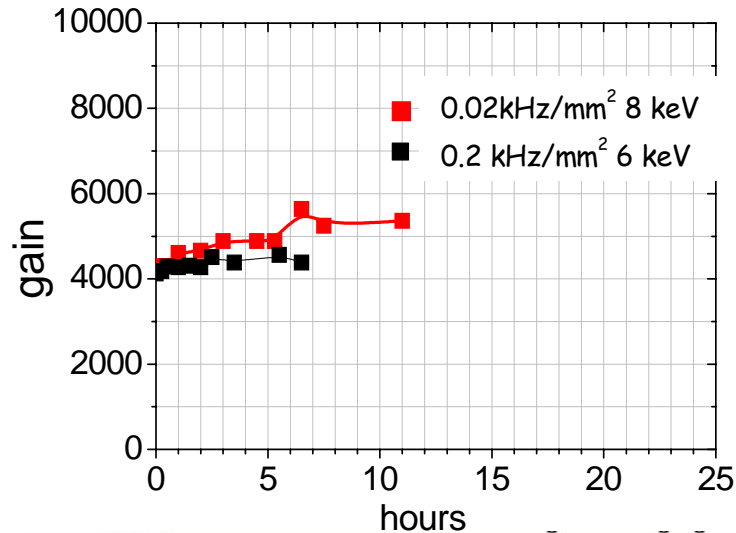
Gain =  $6 \times 10^3$



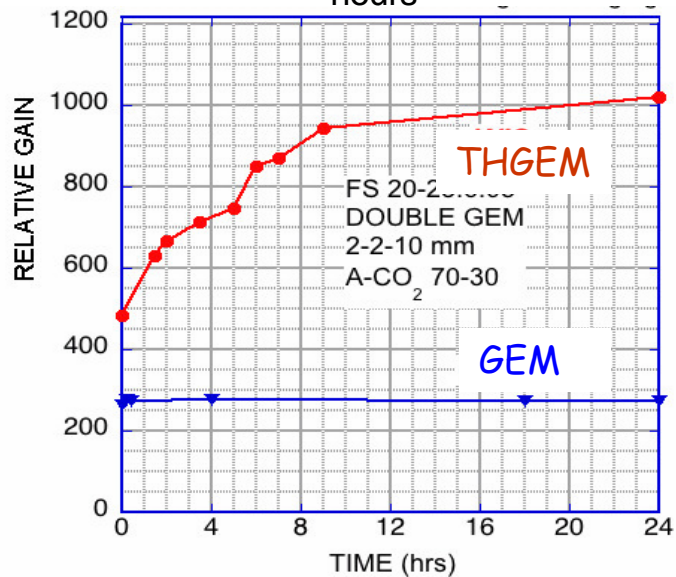
0.4mm thick,  
0.5mm  $\varnothing$  holes,  
1mm pitch  
**Sub-mm resolution !**



# Long-term stability



Our  $10 \times 10 \text{ cm}^2$  double THGEM detector  
 Ar/CH<sub>4</sub>, 6 & 8 keV x-rays, low rate  
 ~25% changes



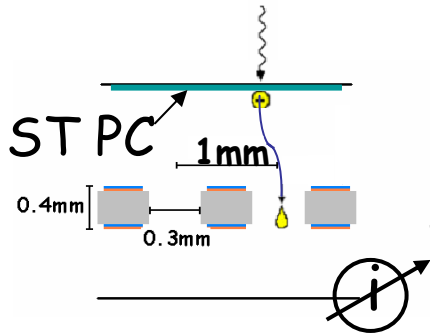
Sauli:  
 double THGEM, Ar/CO<sub>2</sub>, 6keV x-rays,  
 1kHz/mm<sup>2</sup>.  
 Stabilize ~12 hours, x2 gain rise.

- Charging up?
- Insulator polarization?

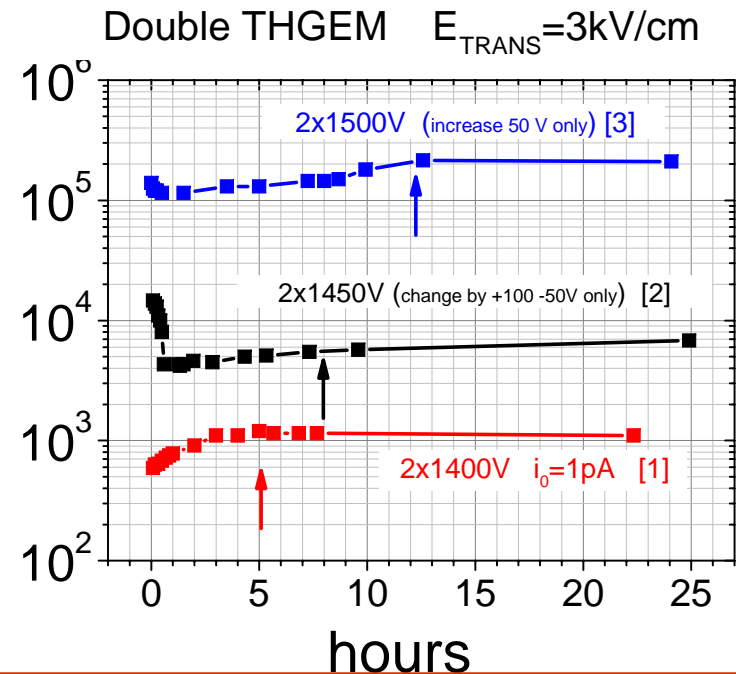
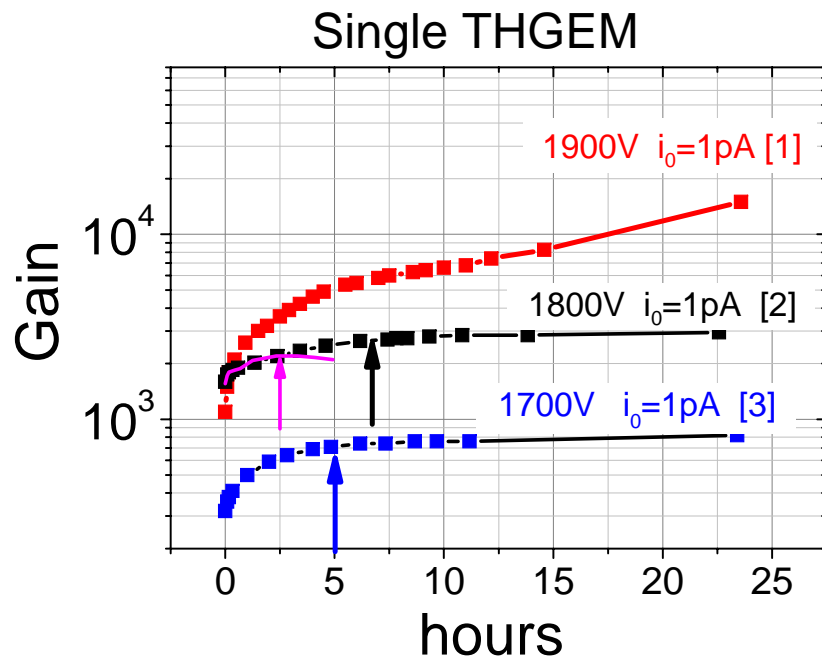
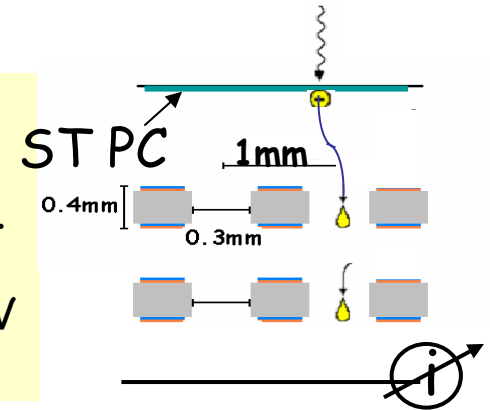
results from  
 HV? Rate? total current? history?



# Long-term stability (2)



- Measured currents w UV + ST PC.
- $E_{\text{drift}} = 0.15 \text{ kV/cm}$ .
- Initial flux  $5 \times 10^5 \text{ e}^-/\text{mm}^2$  ( $\sim 1 \text{ kHz/mm}^2$  x-ray).  
Could not be raised due to PC decay.
- Possible additional effects from p, temp & HV instability.

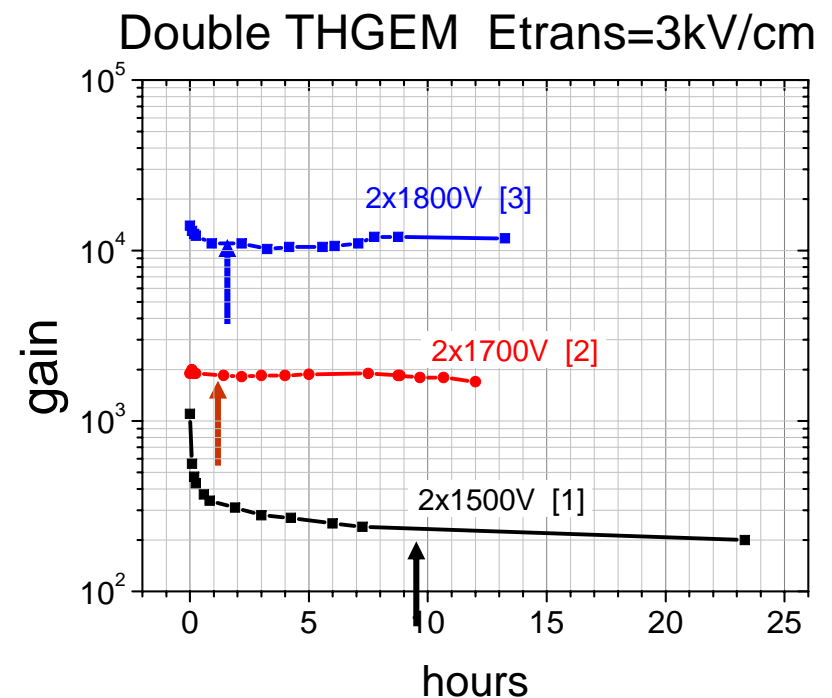
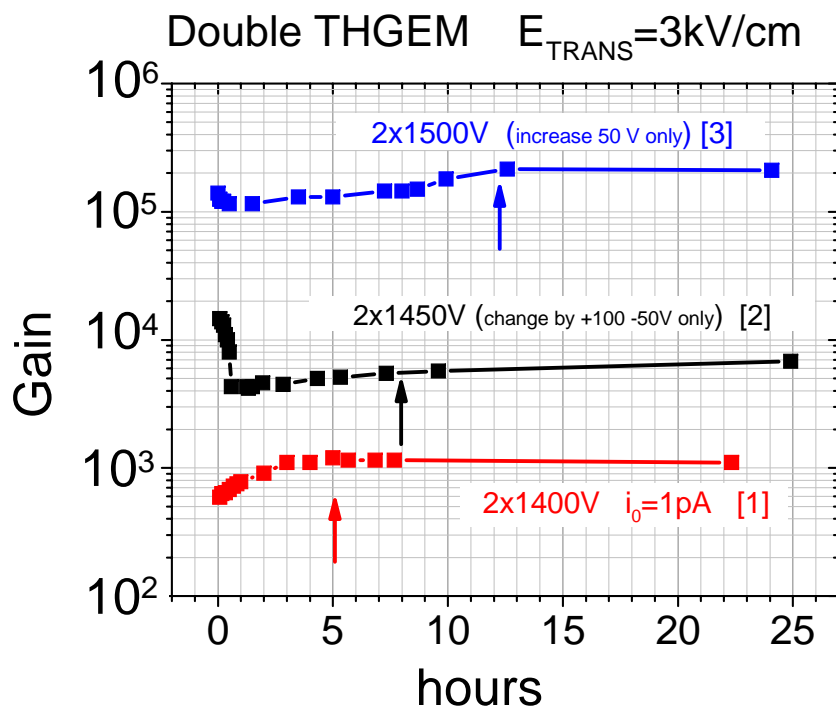


- THGEMs require a few hours of stabilization.
- Stabilization time depends on total gain/current.
- gain variation  $\sim$  factor 2.
- could depend on history (time after THGEM & gas introduction).

# Long-term stability (3)

0.4mm thick,  
0.3mm  $\varnothing$  holes,  
1mm pitch

0.4mm thick,  
0.6mm  $\varnothing$  holes,  
1mm pitch



- Larger hole  $\rightarrow$  shorter stabilization time. Effect of the bare insulator??
- Evidence for combined dependence on history + total gain/current



# Planned studies

1. Systematic study on **long-term stability** vs. **rate** (with x-ray).
2. Understanding the **effect of the 0.1 mm rim** (e.g. reduce it).
3. Studying THGEMs of different **materials**;  
e.g. **CIRLEX** = polyimide (Kapton).



# Applications

LARGE-AREA DETECTORS, ROBUST, MODERATE COST

ns, sub-mm, MHz/mm<sup>2</sup>

- **Particle** tracking at moderate (sub-mm) resolutions.  
e.g. muon-detector @LHC2.
- **TPC** readout.
- Sampling elements in **calorimetry**. (ILC??)
- Readout of light from LXe detector (XENON).
- Moderate-resolution, fast (ns) **X-ray** and **n** imaging.
- **Single-photon** imaging.  
e.g. Ring Imaging Cherenkov (**RICH**) detectors (presently w GEMs).

advantages: robust,  
high eff. for single photons,  
low sensitivity to ionizing BG.

